

ABSTRACT

A method of forming a tapered V-groove in a <100> silicon substrate is described. Spaced apart pits are dry etched in the substrate and sidewalls of the pits are masked. Then, sections of the substrate are wet-etched to connect the spaced apart pits. Each successive wet-etched section has a different width, and hence depth, than the preceding wet-etched section. In one aspect, each succeeding wet-etched section is not as wide, and hence more shallow, than the preceding wet-etched section. Also, each succeeding pit has a smaller cross-sectional area than the preceding pit.